

4Gbit DDR4 DRAM

Extended Temperature Range Targeting Industrial, Automotive, and Communications Markets

MILPITAS, Calif., July 26, 2016 -- Integrated Silicon Solution, Inc. (ISSI), a leader in advanced memory solutions, today announced it has begun sampling production units of its new 4-gigabit (4Gbit) DDR4 DRAM. The 4Gbit DDR4 device is IS43QR16256A (IS46QR16256A for automotive grade), and it is organized as 256Mbx16, packaged in a 96-ball BGA, and operates at 1.2V. ISSI's DDR4 provides low power, high bandwidth, high performance and high reliability needed for leading edge networking, automotive, and industrial systems. This is the first DDR4 DRAM from ISSI, and adds to ISSI's extensive selection of DRAMs. ISSI is offering the DDR4 with the long lifecycle product support required by customer applications in Automotive, Industrial, Communications, and other market segments.

"Today's networking systems constantly need higher bandwidth due to tremendous growth in network traffic; and higher (Industrial) temperature support. Industrial and Automotive customers are also seeking more data throughput, along with high reliability and a wide range of temperature support for rugged applications," said Anand Bagchi, Director of Strategic Marketing at ISSI.

"Many of the applications are adopting DDR4 not only because of increased data throughput with lower power, but also due to the new features in DDR4 like CRC for error detection and Boundary Scan that add data integrity and reliability," said Chuck McLaren, Director of DRAM Marketing at ISSI.

In addition to the new DDR4, ISSI offers a broad line of SDR, mobile SDR/DDR, DDR, DDR2, and DDR3 products, 256Kb-4Gb automotive grade flash memory products as well as a comprehensive line of asynchronous and synchronous SRAMs with densities from 64Kb to 72Mb, and analog & mixed signal products. And ISSI supports a range of Known Good Die (KGD) devices in its portfolio.

About Integrated Silicon Solution, Inc.

ISSI is a fabless semiconductor company that designs and markets high performance integrated circuits for the following key markets: (i) automotive, (ii) communications, (iii) industrial/medical, and (iv) digital consumer. The Company's primary products are high speed and low power SRAM and low, medium, and high density DRAM. The Company also designs and markets Serial/Parallel NOR and SLC NAND Flash Products and high performance analog and mixed signal integrated circuits. ISSI is headquartered in Silicon Valley with worldwide offices in Taiwan, Japan, Singapore, China, Europe, Hong Kong, India, and Korea. Visit our web site at http://www.issi.com/

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